

**Title of Article:** Determination of Characteristic Relaxation Times And Their Significance In Copper Oxide Thin Film

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**Abstract:** The copper oxide thin film was characterized using both the theoretical and experimental approach at different oxidation temperatures between 1500C to 4500C. Two experimental methodologies were combined with theoreoccal model to invesogate the effect of time relaxations on the samples. The time relaxation of the current predicted the suitability of the sample to be used to fabricate either solar cell or semiconductor. The time relaxation of the voltage showed the degree of disorderliness created within the sample during fabrication.